

ABSTRACT OF THE DISCLOSURE

For crystallizing an amorphous semiconductor film by means of irradiation of laser beams, a top surface and a back surface of the amorphous semiconductor film are irradiated with the laser beams. In this case, an effective energy intensity I_0 of the laser beams to be applied onto the top surface and an effective energy intensity I_0' of the laser beams to be applied onto the back surface satisfy the relationship of $0 < I_0'/I_0 < 1$ or $1 < I_0'/I_0$. Thus, a laser annealing method capable of providing a crystalline semiconductor film with large grain diameters can be provided.

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